上海交通大學

年 月 日
VESII Homework 5. FEIR
uestion 1.
A). VBS-VAN= 5-1/2-0.7 Since VDS > VBS-V4h, it's in saturation
Apply the firmula: Ix= 7.286×10-4. (4.3-12)
Ix (A)
0.013
V/2(V)
B). Vas-V4h= 124-0,742 \$1.0,2V.
VO3-VX-1U if VX>1.2V saturation if brevx >2 lv,
felothoziv triode. Ctriode
Par Vaziov. Ix= 2.91X10-5A.
for like 2/1/2 1x>-1.46x6-3 1-2 1/2 + 5)
for over x < v: Ix=-1.46x10-3 (-\$(1-Vx)+(1-Vx).(1.2-Vx)
₩ Z×LA)
2.91×10-3
-1.02 XI0-3
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(C) VDS=VX-1.9, VGS-V+n=-1.6V<0 cutoff. while not raverse,
when reverse: Vps=1.9-Vx. Vgs-V4h= 0.3-Vx>0 => Vx<0.3V.
also Vos > U63-Vth: Seturation.
=> 1x=-7.29x10-4,(0.3-Vx)2.
Ixuf)
0 0.3 2 Vx(V)
-P'ZPM2
(D). Hos= VSD= 190/x-1.9v. while 1/x>1.9v.
Vsg-Vth = 0-10 (Vx-1)-0.8= Vx-1.8 v > Vsp. (tribde region)
Jg- as Vx <1.9v: Vsp: 1.9-Vx. Vs6-[V4h]: 02-16.0.1>0.
Vx>19v: 1x=-1.40 6 x10-3 (-±(1.9-Vx)+0.101.9-Vx))
Vx=1.9v: J when Vx>1.8v (trible) Tx=-7.29 x10-6A
When V==1.8V (seturation). Tx=-1.46 xp-3 (-\frac{1}{2}(1.9-Vx)+a1(1.9-Vx))
7.45×03 7×04)
(81.9)
-1.29×0-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1-1
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Questibn 2		
For MOSFET 1: Vos-Vth= 2.5-V, -0.9=1,6-4		
VDS= J-V => In saturation area.		
1-5Mn Cox Left [Was-V+n. Vox-5-Vox] (VGs-V+n	z.]	
For MOSTE72: Vas-Ver= 1-10-V-V3-0,9 Vos=V1-V	2.	
Assume MoSFB12 in saturation region => V, 5-1	,9 v.	
= (-V2-0,9)(V,-V2)-E(V2+23
=> Vos (0 Rzis off. X.		
so MosfE[2 in triode region > V1>0.9v		
V2+2.5 = (Vas, -V+h)= (Vasz-V+h) => V1 = V2+2	5'2.	
=> dV1=976V		
V> =-1.84V.		

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